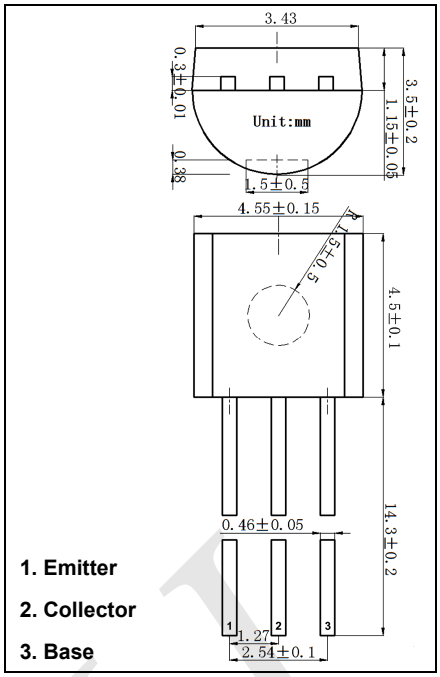
SHENZHEN LONG JING MICRO-ELECTRONICS CO., LTD.

TO-92 Plastic-Encapsulate Transistors

A1015 PNP Transistors



Features

■ Power dissipation

Maximum Ratings (T_a=25°C unless noted otherwise)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector Base Voltage	-50	V
V_{CEO}	Collector Emitter Voltage	-50	V
V_{EBO}	Emitter Base Voltage	-5	V
I_C	Collector Current	-150	mA
P_D	Collector Power Dissipation	400	mW
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55 ~ +150	°C
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	312	°C/W

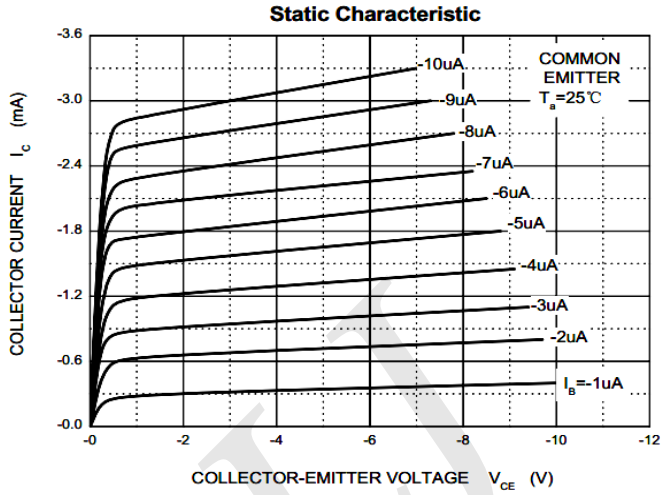
Electrical Characteristics (T_a=25°C unless otherwise specified)

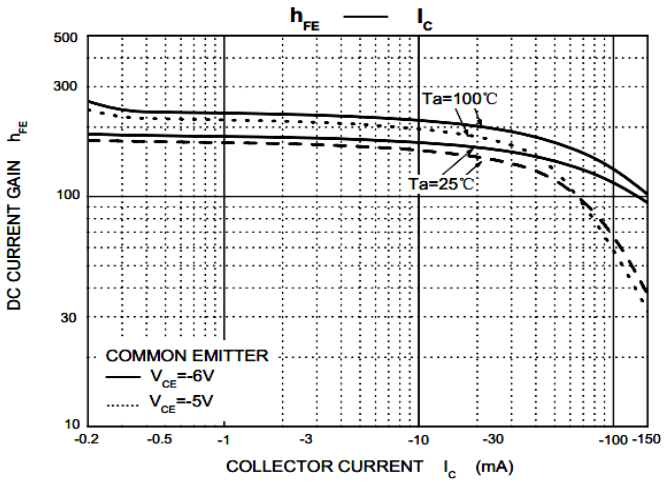
Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C = -100μA,I_E = 0	-50			V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C = -0.1mA,I_B = 0	-50			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E = -100μA,I_C = 0	-5			V
I_{CBO}	Collector cut-off current	V_{CB} = -50V,I_E = 0			-100	nA
I_{CEO}	Collector cut-off current	V_{CE} = -50V,I_B = 0			-100	nA
I_{EBO}	Emitter cut-off current	V_{EB} = -5V,I_C = 0			-100	nA
$h_{FE(1)}$	DC current gain	V_{CE} = -5V, I_C = -1mA	70		400	
$h_{FE(2)}$		V_{CE} = -6V, I_C = -2mA	70			
$V_{CE(sat)}$	Collector-emitter saturation voltage	I_C = -100mA,I_B = -10mA			-0.3	V
$V_{BE(sat)}$	Base-emitter saturation voltage	I_C = -100mA,I_B = -10mA			-1.1	V
f_T	Transition frequency	V_{CE}=-10V,I_C=-1mA,f=30MHz	80			MHz
C_{ob}	Collector Output Capacitance	V_{CB} = -10V, I_E = 0,f = 1MHz			7	pF
NF	Noise figure	V_{CE} = -6V, I_C = -0.1mA, f =1kHz, R_G = 10kΩ			6	dB

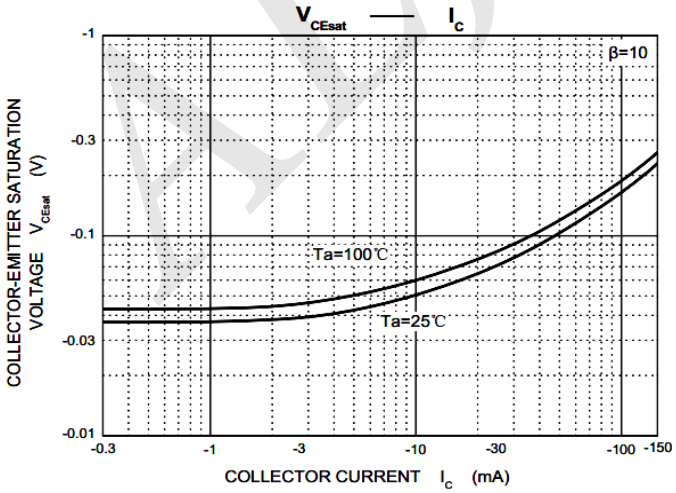
Classification OF $h_{FE(1)}$

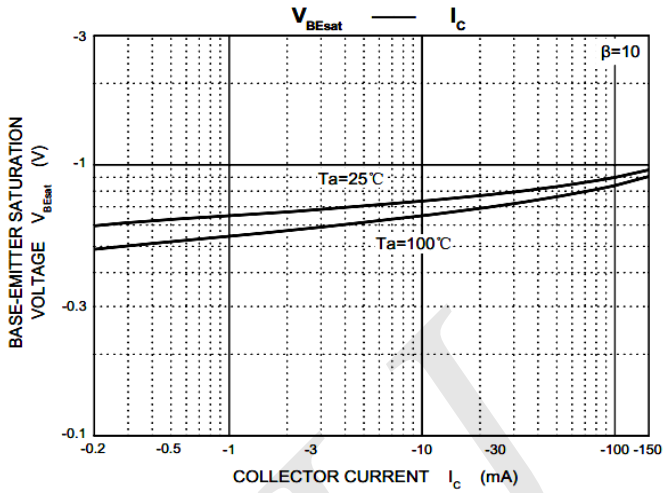
Rank	O	Y	GR
Range	70-140	120-240	200-400

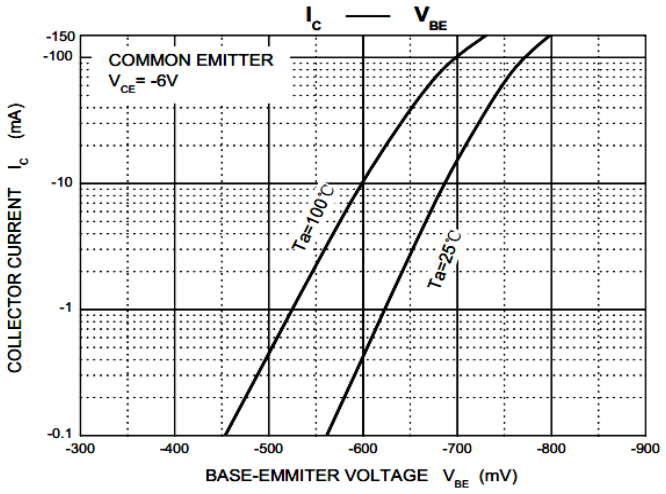
Typical Characteristics

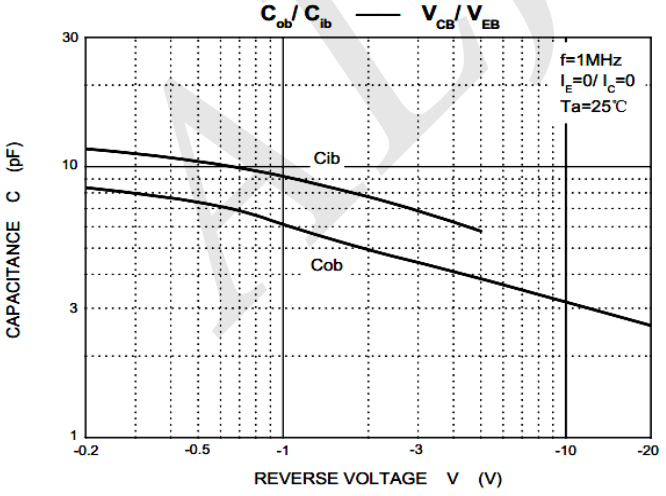


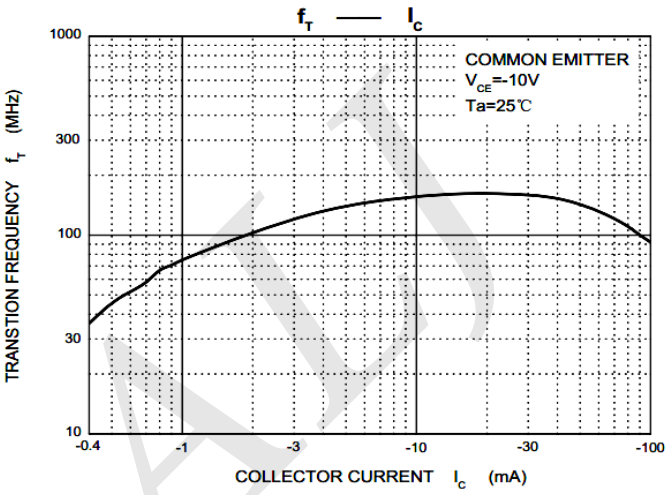


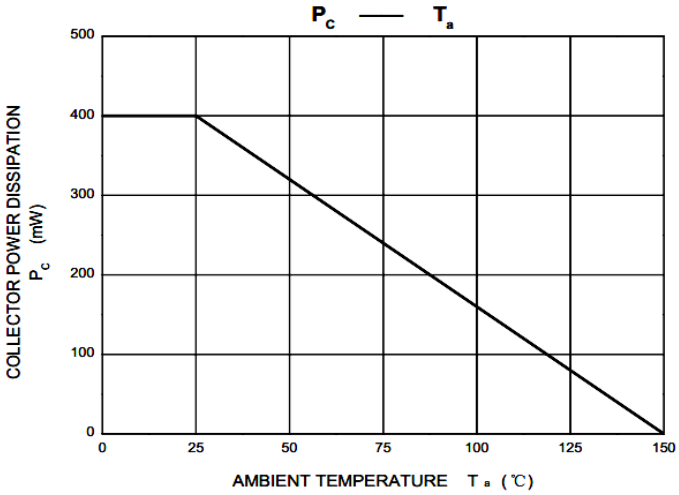












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